3 1200 volts class IGBT modules

- The turnoff time is one tenth or less that of bipolar transistors, enabling a high conversion ferquency for power converters.
- The voltage drive element enables the drive circuit to be miniaturized and used in common.
- Because the safe operating area is wide at turnoff, operation is possible at margins under high voltage.

Device type	V_{CES} volts	V_{GES} volts	I_C cont. amps.	P_C watts	V_{CE}(sat) Max. volts	(V_{GE}=15V) I_C amps.	Switching time (Max.) t_{on} μsec.	t_{off} μsec.	t_f μsec.	Package	Net weight grams	Equivalent circuit (Pege 40)
2MBI25-120	1200	±20	25	250	5.0	25	1.2	1.5	1.0	M211	210	Fig. H2
2MBI50-120	1200	±20	50	400	5.0	50	1.2	1.5	1.0	M211	210	Fig. H2
2MBI75-120	1200	±20	75	600	5.0	75	1.2	1.5	1.0	M212	275	Fig. H2
2MBI100-120	1200	±20	100	800	5.0	100	1.2	1.5	1.0	M213	395	Fig. H2
2MBI150-120	1200	±20	150	1200	5.0	150	2.0	2.0	1.0	M210	470	Fig. H2
1MBI200-120	1200	±20	200	1600	5.0	200	2.0	2.0	1.0	M106	460	Fig. H1
1MBI300-120	1200	±20	300	2000	5.0	300	2.0	2.0	1.0	M106	460	Fig. H1

4 1200 volts class 6-pack IGBT modules

- 6 IGBTs and 6 free wheel diodes are built into one package.
- Optimal for miniaturizing and reducing the weight of three-phase 440 to 480 volts input inverters.

Device type	V_{CES} volts	V_{GES} volts	I_C cont. amps.	P_C watts	V_{CE}(sat) Max. volts	(V_{GE}=15V) I_C amps.	Switching time (Max.) t_{on} μsec.	t_{off} μsec.	t_f μsec.	Package	Net weight grams	Equivalent circuit (Page 40)
6MBI8-120	1200	±20	8	60	5.0	8	1.2	1.5	1.0	M604	150	Fig. H3
6MBI15-120	1200	±20	15	120	5.0	15	1.2	1.5	1.0	M607	235	Fig. H4
6MBI25-120	1200	±20	25	250	5.0	25	1.2	1.5	1.0	M608	510	Fig. H5
6MBI50-120	1200	±20	50	400	5.0	50	1.2	1.5	1.0	M608	510	Fig. H5